

NLG4137

12.5 Gb/s 2 - INPUT AND / NAND

(Output : RZ Format)

The NLG4137 is an ultra-fast 2 input AND / NAND operating at up to 12.5 Gb/s (MIN.) . It is designed with LSCFL (Low-power Source Coupled FET Logic) , it uses SCFL I/O levels (V_H : 0.0 V, V_L : -0.9V) .

Owing to built-in 50-ohm termination resistors between signal input pins and ground (GND), external termination resistors are unnecessary for impedance matching .

The NLG4137 is fabricated using the 0.15- μ m gate length A-SAINT (Advanced Self-Aligned Implantation for N⁺ layer Technology) process .

FEATURES

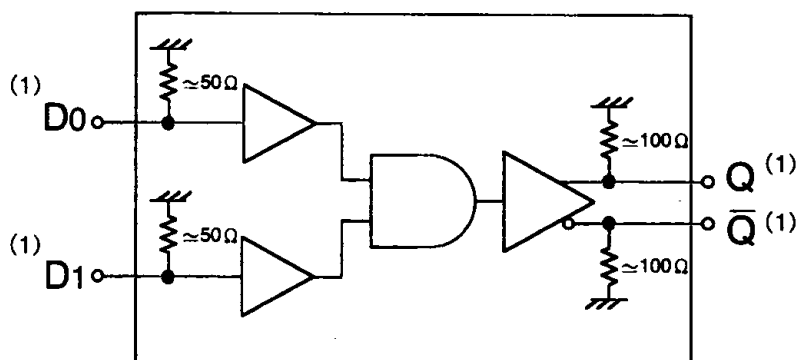
Ultra-high speed : maximum operating speed $f_{MAX} = 12.5$ Gb/s [MIN.]
 output rise time $t_r = 20$ ps (20-80%) [TYP.]
 output fall time $t_f = 20$ ps (20-80%) [TYP.]

High Reliability : hermetically-sealed package

APPLICATIONS

- Basic circuit for various logic circuits
- Line Driver
- 2-phase clock generator
- Line Receiver
- Gating Circuit
- High Speed Comparator

FUNCTIONAL DIAGRAM



Note (1) DC coupling (see page 9)

TRUTH TABLE

D0	D1	Q	\bar{Q}
L	L	L	H
L	H	L	H
H	L	L	H
H	H	H	L

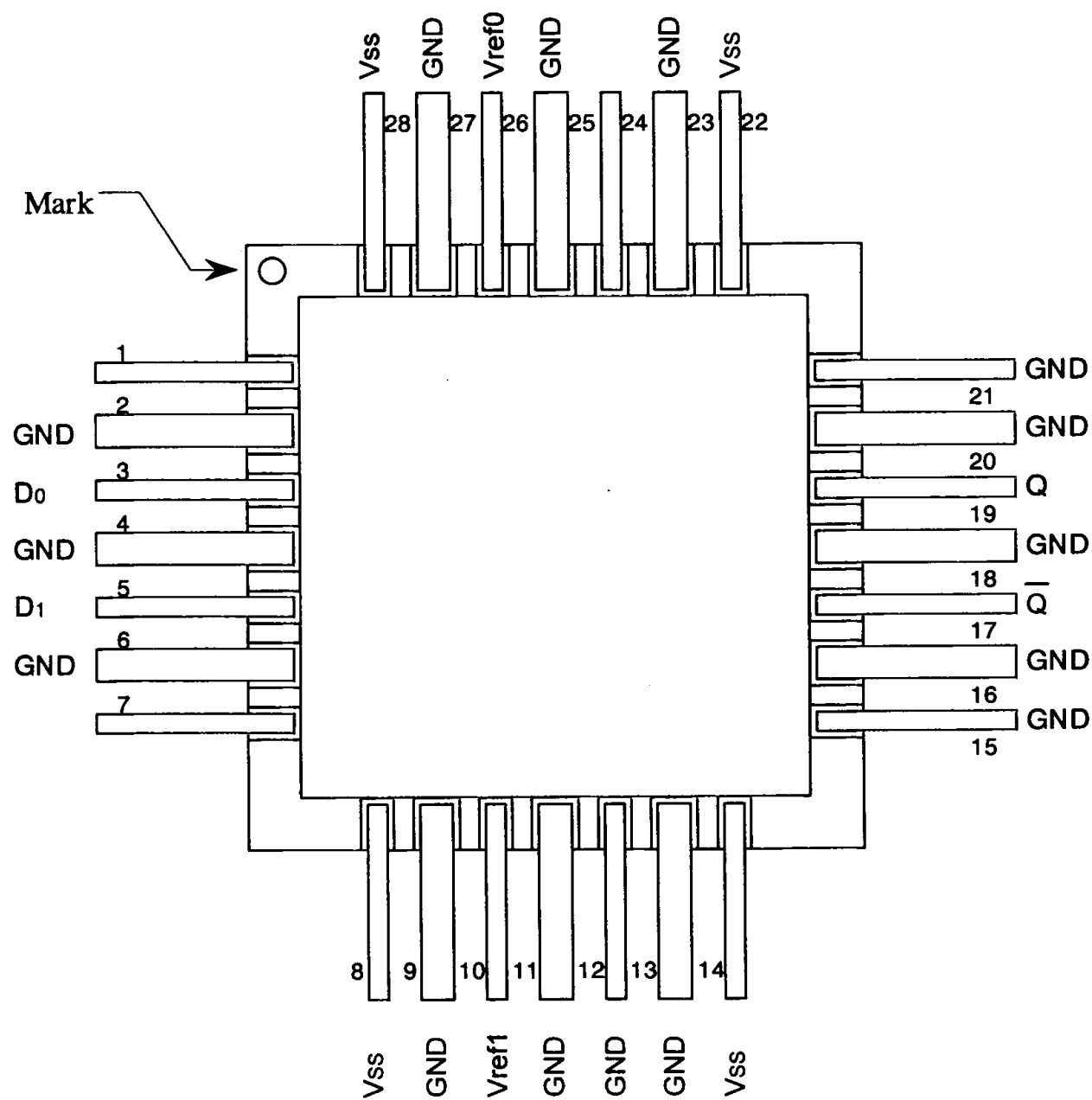
PIN CONNECTION TABLE

PIN No.	NAME	FUNCTION	PIN No.	NAME	FUNCTION
1	N.C.	No Internal Connection	15	GND	Ground (0.0 V)
2	GND	Ground (0.0 V)	16	GND	Ground (0.0 V)
3	D ₀	Signal Input 0	17	\bar{Q}	Data Output (Comp.)
4	GND	Ground (0.0 V)	18	GND	Ground (0.0 V)
5	D ₁	Signal Input 1	19	Q	Data Output (True)
6	GND	Ground (0.0 V)	20	GND	Ground (0.0 V)
7	N.C.	No Internal Connection	21	GND	Ground (0.0 V)
8	V _{SS}	Power Supply (-3.5V)	22	V _{SS}	Power Supply (-3.5V)
9	GND	Ground (0.0 V)	23	GND	Ground (0.0 V)
10	V _{ref1}	D ₁ Input Ref. ⁽¹⁾	24	N.C.	No Internal Connection
11	GND	Ground (0.0 V)	25	GND	Ground (0.0 V)
12	GND	Ground (0.0 V)	26	V _{ref0}	D ₀ Input Ref. ⁽¹⁾
13	GND	Ground (0.0 V)	27	GND	Ground (0.0 V)
14	V _{SS}	Power Supply (-3.5V)	28	V _{SS}	Power Supply (-3.5V)

Notes

- (1) V_{ref0}, V_{ref1} : Internally generated reference voltage that determines the signal input threshold level. By applying - 0.75 V to - 0.2 V externally to this pin, an arbitrary signal input threshold voltage can be established.
- (2) : Terminate unused output pins in 50-ohms.

CONNECTION DIAGRAM (TOP VIEW)



ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING
V _{SS}	Power Supply Voltage	+0.5 V ~ - 4.0 V
V _{IN}	Applied Voltage at Signal Inputs (D ₀ , D ₁)	+0.3 V ~ - 1.6 V
V _{OUT}	Applied Voltage at Signal Outputs (Q, \overline{Q})	+0.2 V ~ - 1.75 V
V _{ref0} , V _{ref1}	Applied Voltage at V _{ref0} and V _{ref1} pins	+0.3 V ~ - 1.6 V
T _{stor}	Storage temperature	- 60 °C ~ +150 °C
T _C (1)	Case temperature under Bias	- 60 °C ~ +125 °C

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT'S
V _{SS}	Power Supply Voltage	- 3.75	- 3.5	- 3.4	V
V _{ref0} , V _{ref1}	Applied Voltage at V _{ref0} and V _{ref1} pins	Adjust in the range from -0.75 V to -0.20 V			V
V _{IN}	Signal Input Interface (D ₀ , D ₁)	DC Coupling (SCFL)			—
V _{OUT}	Signal Output Interface (Q, \overline{Q})	DC Coupling , Terminate to GND through 50Ω			—

DC CHARACTERISTICS

(V_{SS} = - 3.75 V ~ - 3.4 V, GND = 0.0 V, T_c = 0 ~ 85 °C (1))

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT'S
V _{OH}	Output Voltage, High (Q, \overline{Q})	- 0.1	0.0		V
V _{OL}	Output Voltage, Low (Q, \overline{Q})		- 0.9	- 0.85	V
V _{IH}	Input Voltage, High (D ₀ , D ₁)	- 0.2	0.0		V
V _{IL}	Input Voltage, Low (D ₀ , D ₁)		- 0.9	- 0.75	V
I _{SS}	Power Supply Current		500	730	mA (2)
P _d	Power Dissipation		1.8	2.7	W (2)

Notes

(1) T_c : temperature at package base.

(2) : Includes load current. Excludes current through input termination resistors, all of which have a value of 50 - ohms.

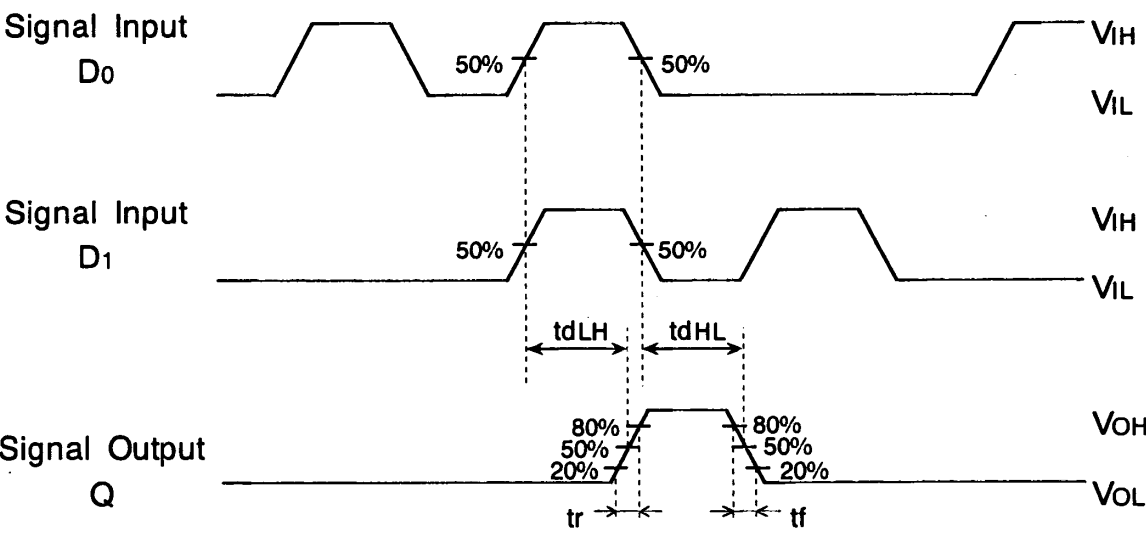
AC CHARACTERISTICS

($V_{SS} = -3.75\text{ V} \sim -3.4\text{ V}$, $GND = 0.0\text{ V}$, $T_c = 0 \sim 85\text{ }^{\circ}\text{C}$, V_{ref0} : Adjust in the range from -0.75 V to -0.2 V , V_{ref1} : Adjust in the range from -0.75 V to -0.2 V)

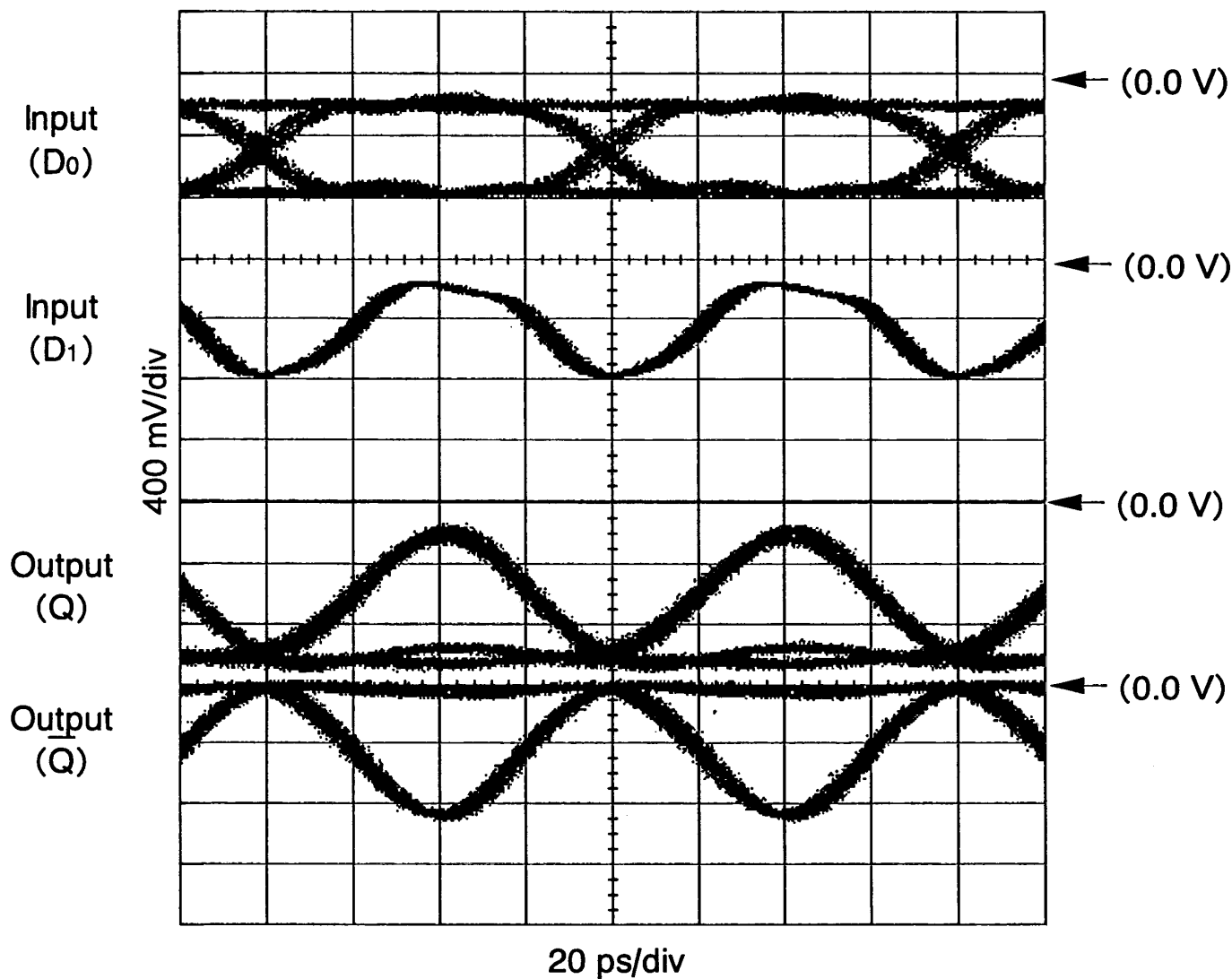
SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNITS	
f_{MAX}	Maximum Data Operating Speed	12.5			Gb/s	(1)
t_r	Output Rise Time (Q, \overline{Q})		20	40	ps	(2)
t_f	Output Fall Time (Q, \overline{Q})		20	40	ps	(3)
t_{dLH}	Output Rise Delay	205	235	260	ps	(3)
t_{dHL}	Output Fall Delay	205	235	260	ps	(3)

Notes

- (1) Measurement Condition : $f = 12.5\text{ Gb/s}$, Output : RZ Format
- (2) Confirmed by error-free operation using a pseudo-random pattern having a word length of $2^{23}-1$ bits .
- (3)



SAMPLE OUTPUT WAVEFORMS (12.5 Gb/s, RZ Format)

Measurement Conditions

$T_a = 25^\circ\text{C}$

$V_{ss} = -3.5\text{ V}$

$V_{ref0} = -0.5\text{ V}$

$V_{ref1} = -0.5\text{ V}$

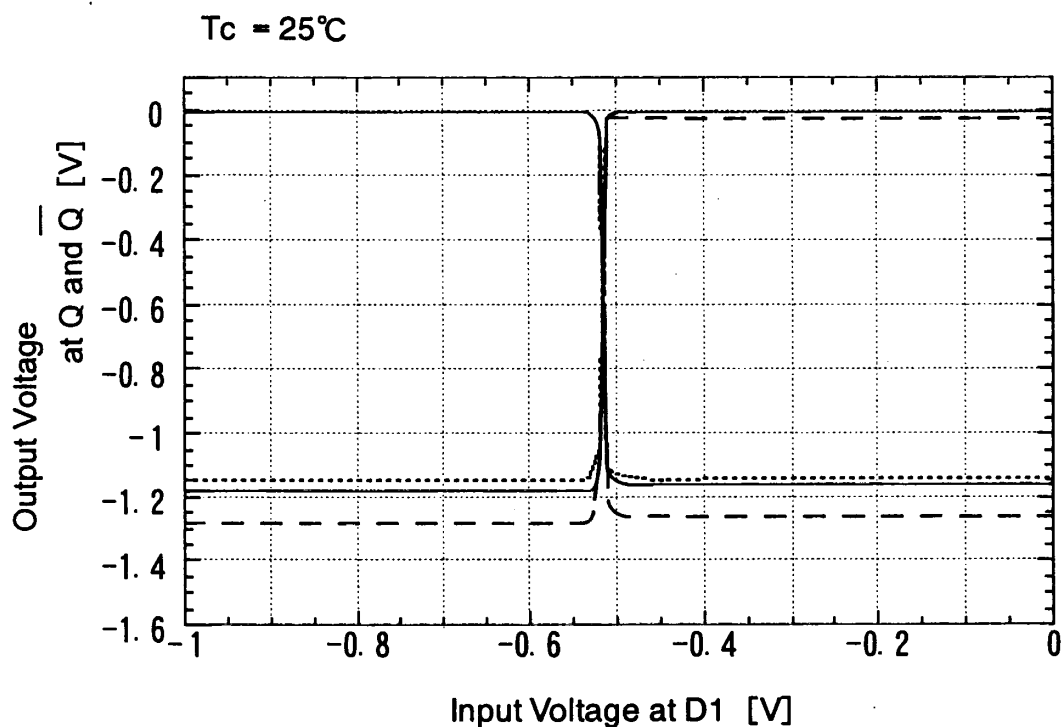
D0 : 12.5 Gb/s, PN = 23, MR = 1/2, $V_{IH} = -0.2\text{ V}$, $V_{IL} = -0.75\text{ V}$

D1 : 12.5 GHz, $V_{IH} = -0.2\text{ V}$, $V_{IL} = -0.75\text{ V}$

Signal outputs connected to the 50-ohm impedance pins of a sampling oscilloscope.

Results given here were obtained using the NEL test fixture.

SAMPLE DC TRANSFER CHARACTERISTICS



..... : $V_{ss} = -3.40\text{ V}$
 ————— : $V_{ss} = -3.50\text{ V}$
 - - - - - : $V_{ss} = -3.75\text{ V}$

Measurement Conditions

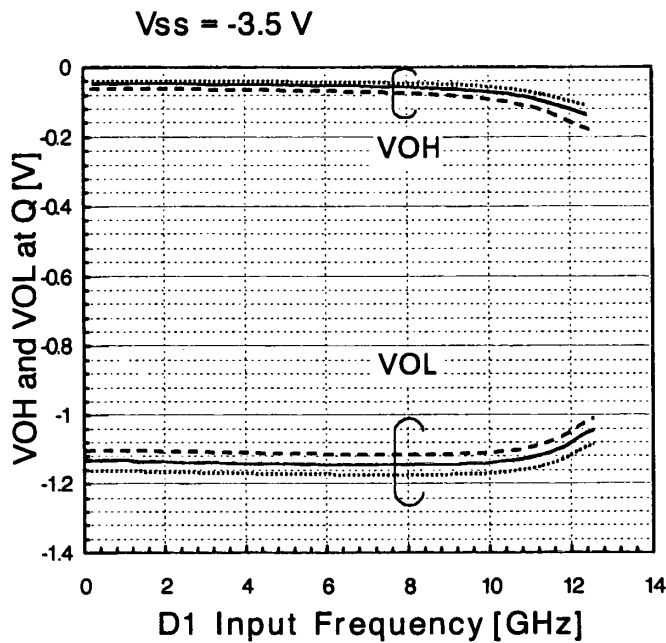
$D_0 : -0.2\text{ V}$

$V_{ref1} = -0.5\text{ V}$

$V_{ref2} = -0.5\text{ V}$

Results given here were obtained using the NEL test fixture.

SAMPLE AC CHARACTERISTICS

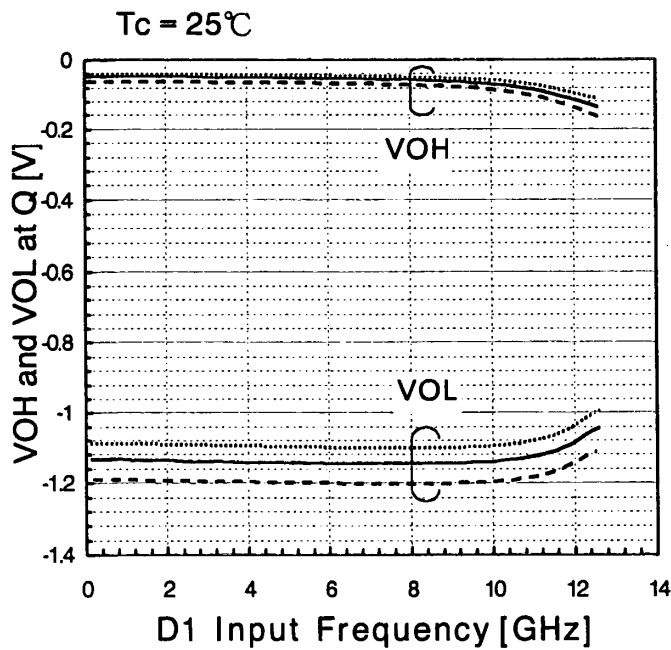


- : T_c = 0 °C
- : T_c = 25°C
- : T_c = 85°C

Measurement Conditions

D0 : PN = 23, MR = 1/2,
VIH = -0.2 V, VIL = -0.75 V,
D1 : VIH = -0.2 V, VIL = -0.75 V,
Vref1 = -0.5V
Vref2 = -0.5V

Results given here were obtained
using the NEL test fixture.



- : V_{ss} = -3.40V
- : V_{ss} = -3.50V
- : V_{ss} = -3.75V

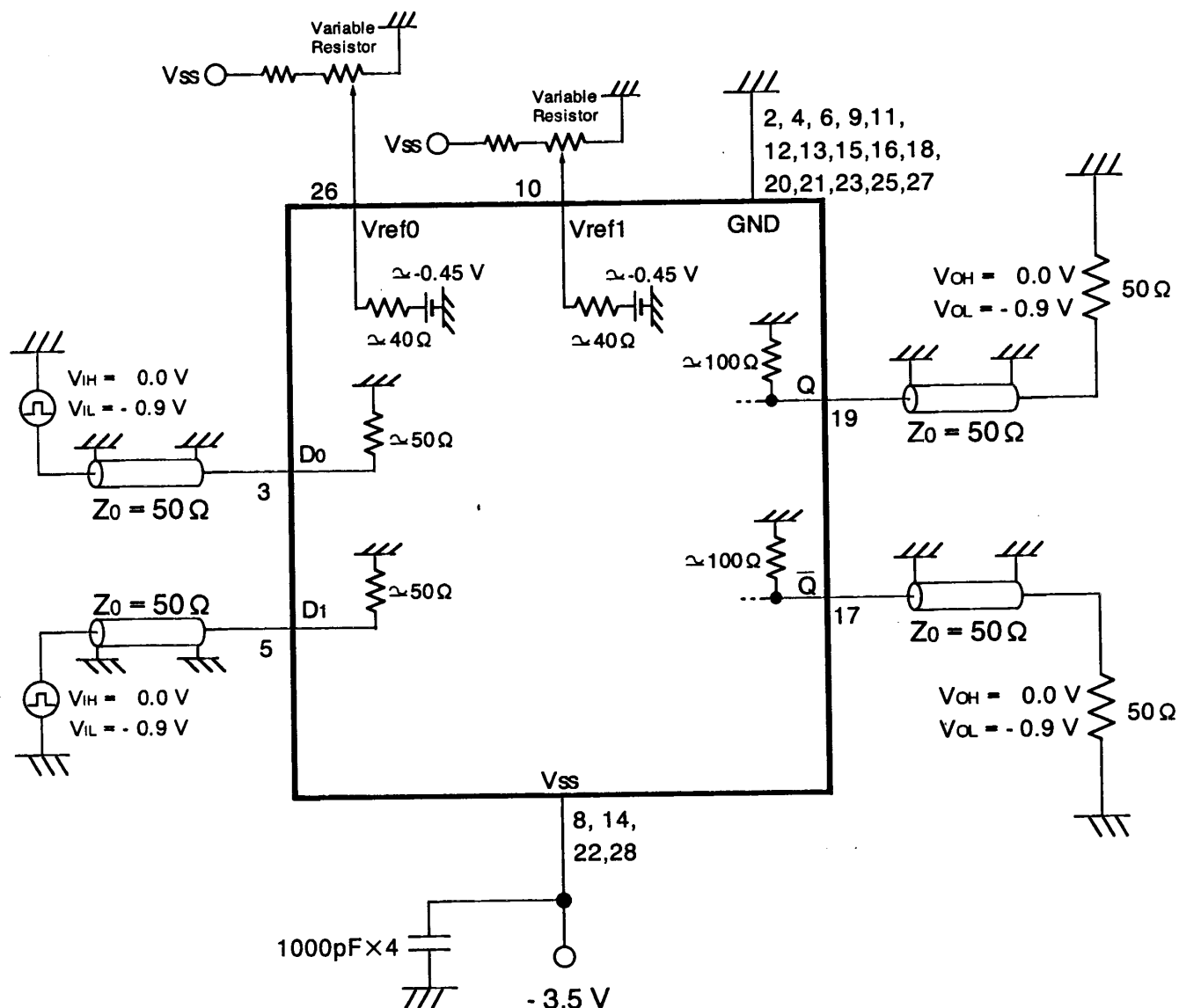
Measurement Conditions

D0 : PN = 23, MR = 1/2,
VIH = -0.2 V, VIL = -0.75 V,
D1 : VIH = -0.2 V, VIL = -0.75 V,
Vref1 = -0.5V
Vref2 = -0.5V

Results given here were obtained
using the NEL test fixture.

SAMPLE IMPLEMENTATION

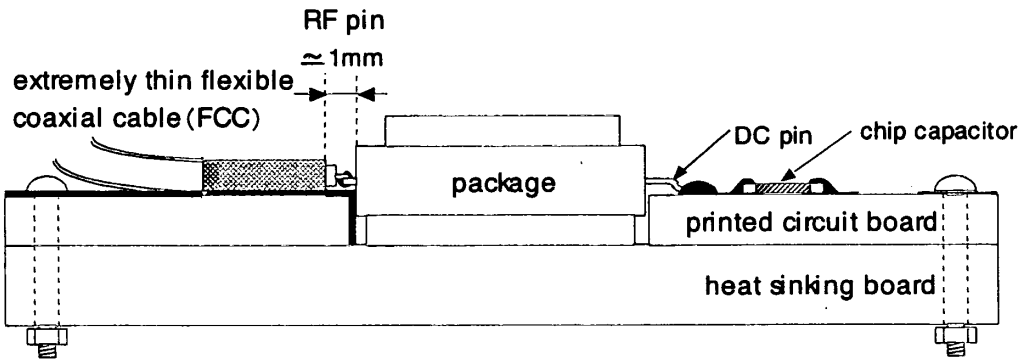
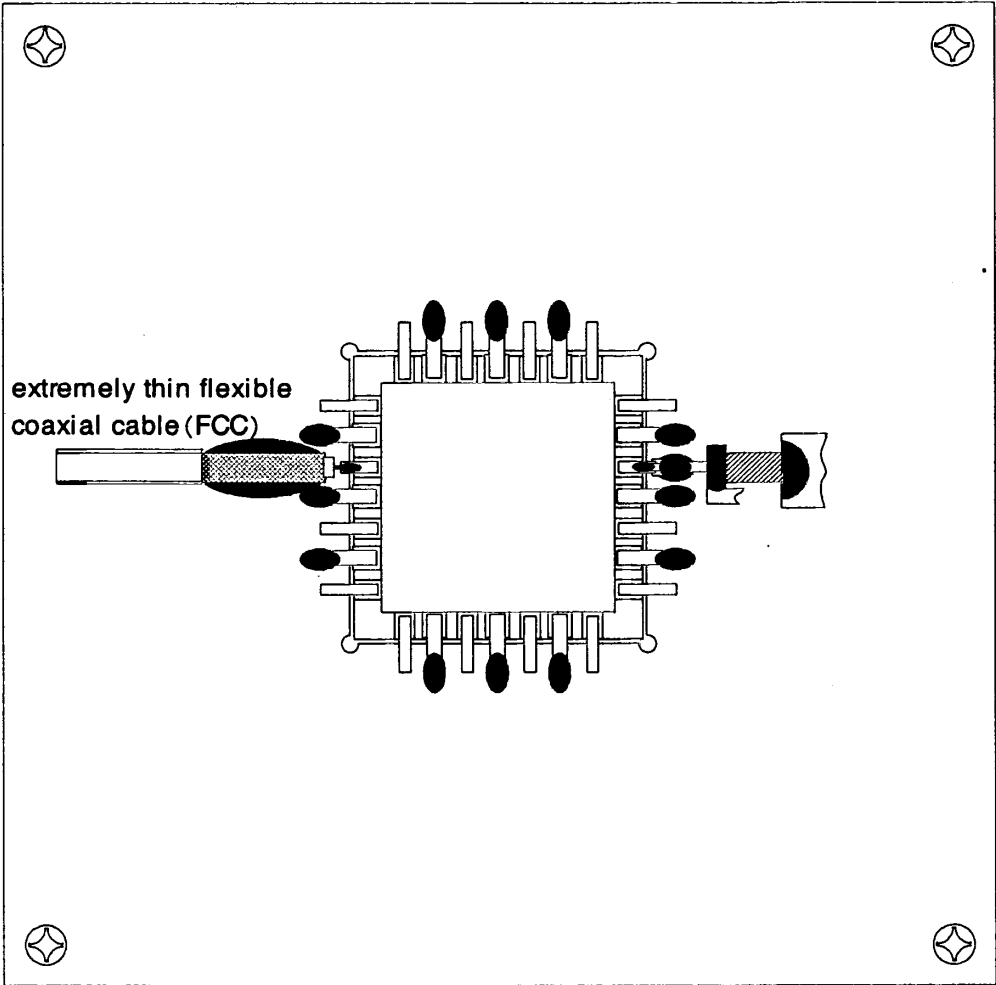
Note : Numbers represent pin numbers



Although not shown here, in place of the above variable resistors, the Vref0 and Vref1 pins can be connected directly to an external power supply.

In this case, apply approximately -0.5 V.

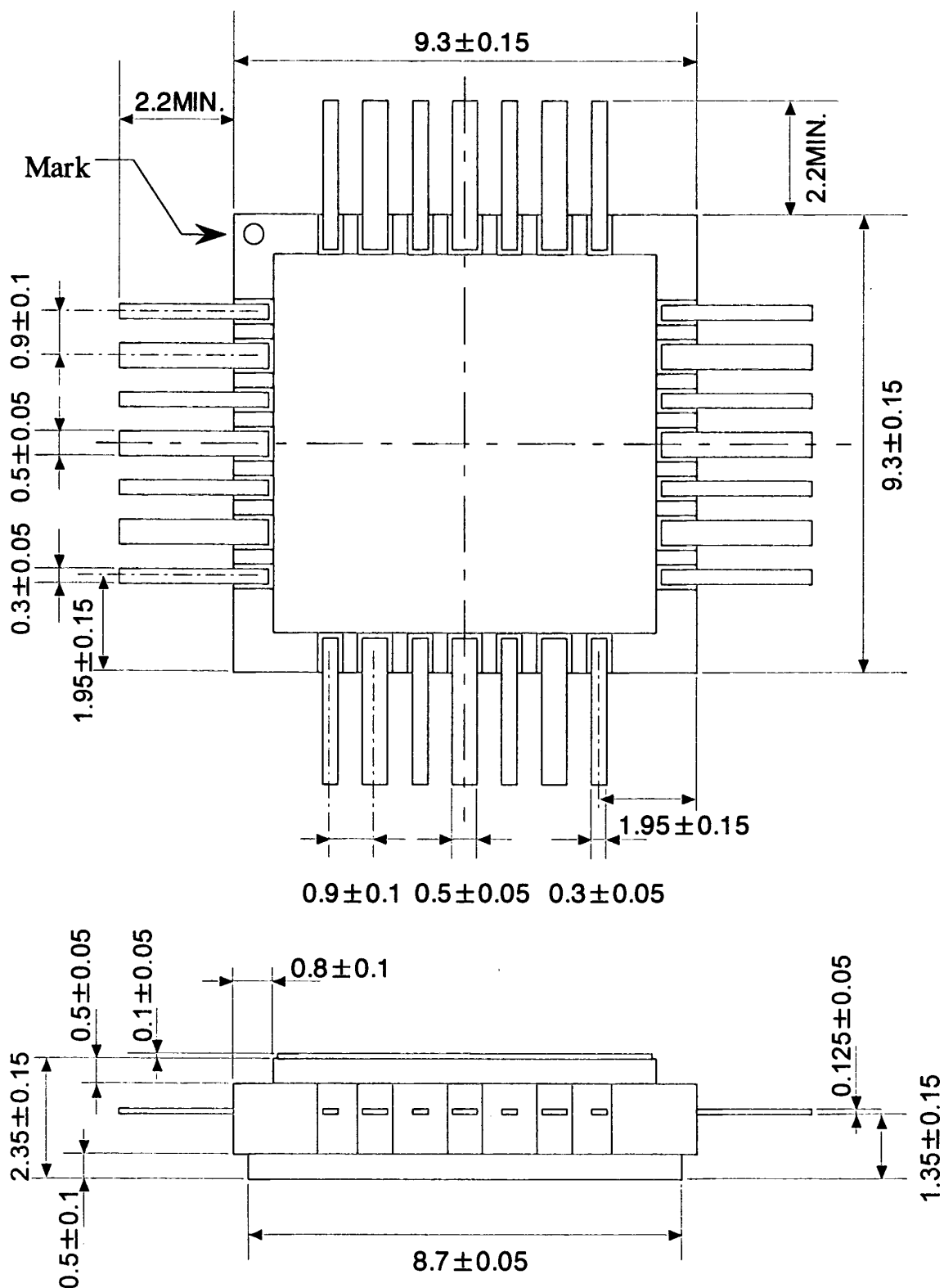
SAMPLE MOUNTING



 : solder

Caution : The package base should be connected to the ground.

TB 28 - PIN PACKAGE DIMENSION (mm)



HANDLING INSTRUCTIONS

Since the NLG4137 is fabricated with GaAs MESFET's (Metal Semiconductor Field Effect Transistors), users are recommended to follow the instructions below to prevent damage to the chip from electro-static discharge.

- 1) Use a conductive working desk connected to the ground (or, a conductive table top connected to the ground).
- 2) Require all handling personnel to wear a conductive bracelet or wrist-strap connected to the ground through a 1 M-ohm resistors.
- 3) Ground all test equipment.
- 4) Ground all soldering iron tips.
- 5) Store IC's and other devices such as chip capacitors in their conductive carriers until they are soldered.

Caution

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